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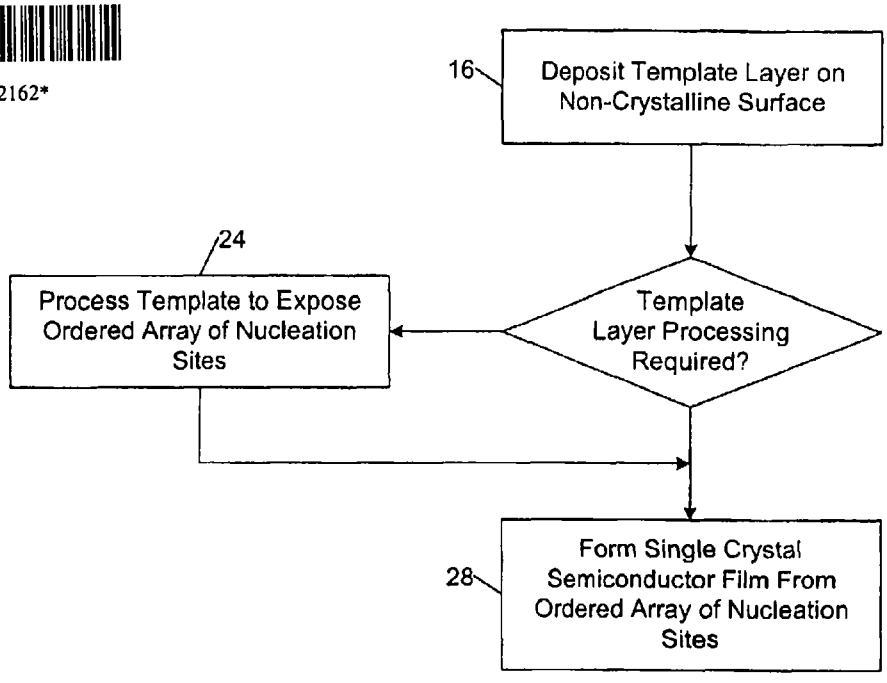
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(54) Title: FORMING A SINGLE CRYSTAL SEMICONDUCTOR FILM ON A NON-CRYSTALLINE SURFACE

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(57) Abstract: A method of forming a single crystal semiconductor film on a non-crystalline surface is described. In accordance with this method, a template layer incorporating an ordered array of nucleation sites is deposited on the non-crystalline surface, and the single crystal semiconductor film is formed on the non-crystalline surface from the ordered array of nucleation sites. An integrated circuit incorporating one or more single crystal semiconductor layers formed by this method also is described.

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